

N-channel TrenchMOS standard level FET

Product data sheet

1. General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using Nexperia High-Performance Automotive (HPA) TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- Q101 compliant
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

3. Applications

- 12 V, 24 V and 42 V loads
- Automotive systems
- DC-to-DC converters
- Engine management
- General purpose power switching
- Motors, lamps and solenoids
- Transmission control

4. Quick reference data

Table 1. C	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	75	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u> ; <u>Fig. 4</u>	-	-	49	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	105	W
Static chara	acteristics	· ·				
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 20 A; T _j = 25 °C; Fig. 12; Fig. 13	-	13.8	18	mΩ
Dynamic ch	naracteristics	· · · · · ·	'			
Q _{GD}	gate-drain charge	I _D = 20 A; V _{DS} = 60 V; V _{GS} = 10 V; Fig. 14	-	14.24	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 49 A; $V_{sup} \le 75$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	118	mJ

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G
4	G	gate		mbb076 S
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK7Y18-75B	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7Y18-75B	71875B

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	75	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	75	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1; Fig. 4</u>	-	49	А
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Symbol	Parameter	Conditions		Min	Max	Unit
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>		-	34.9	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu s$; Fig. 4		-	198	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	105	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					,
I _S	source current	T _{mb} = 25 °C		-	49	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	198	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 49 A; $V_{sup} \le 75$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	118	mJ
E _{DS(AL)R}	repetitive drain-source avalanche energy	Fig. 3	[1][2][3]	-	-	J

Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[3] Refer to application note AN10273 for further information.

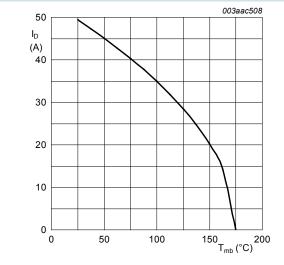
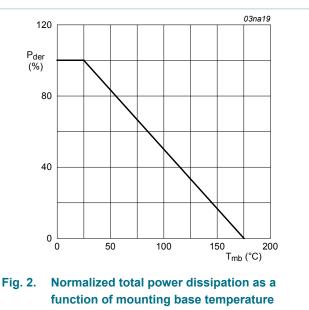


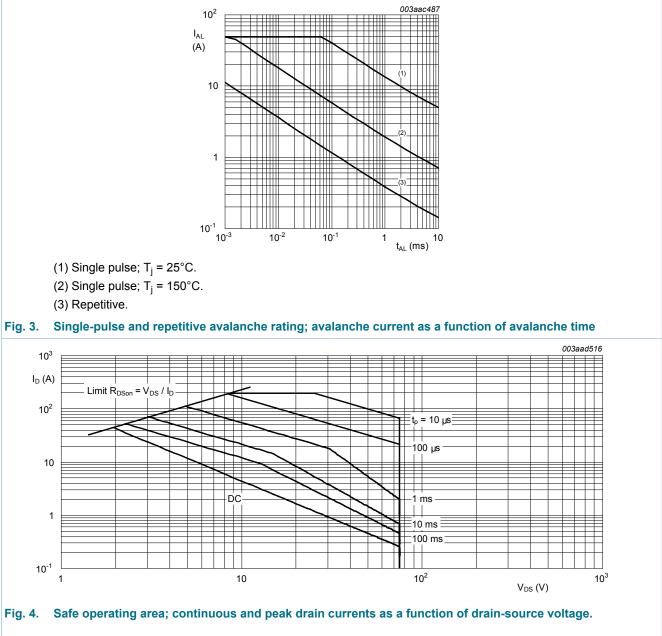
Fig. 1. Continuous drain current as a function of mounting base temperature



 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$

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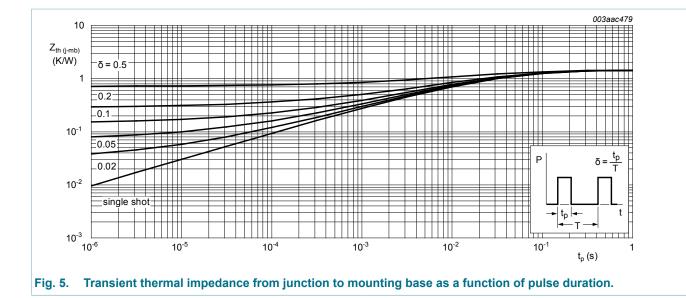
 $T_{mb} = 25 \,^{\circ}C; I_{DM}$ is single pulse

9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	-	1.42	K/W

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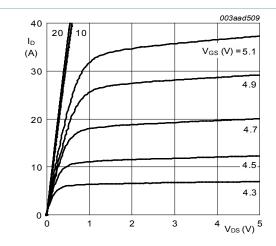
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		I			
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	75	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	68	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 10; Fig. 11	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10	1	-	-	V
I _{DSS} drain leakage current	V_{DS} = 75 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	1	μA	
	V _{DS} = 75 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA	
I _{GSS} gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA	
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 20 A; T _j = 175 °C; Fig. 12; Fig. 13	-	-	43.2	mΩ
		V _{GS} = 10 V; I _D = 20 A; T _j = 25 °C; Fig. 12; Fig. 13	-	13.8	18	mΩ
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	I_D = 20 A; V_{DS} = 60 V; V_{GS} = 10 V;	-	35	-	nC
Q _{GS}	gate-source charge	Fig. 14	-	8.28	-	nC
Q _{GD}	gate-drain charge	1	-	14.24	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;		-	1630	2173	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	274	329	pF
C _{rss}	reverse transfer capacitance	-		-	115	158	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R _L = 1.5 Ω; V _{GS} = 10 V;		-	18.5	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega$		-	22.5	-	ns
t _{d(off)}	turn-off delay time			-	44.5	-	ns
t _f	fall time			-	19.8	-	ns
Source-dra	ain diode	1	I				
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 25 V; T _j = 25 °C; Fig. 16		-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 20 A; dI_{\rm S}/dt = -100 A/µs; V_{\rm GS} = 0 V;		-	55.4	-	ns
Qr	recovered charge	V _{DS} = 30 V		-	143	-	nC





 $T_j = 25 \,^{\circ}C$

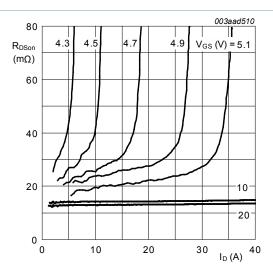
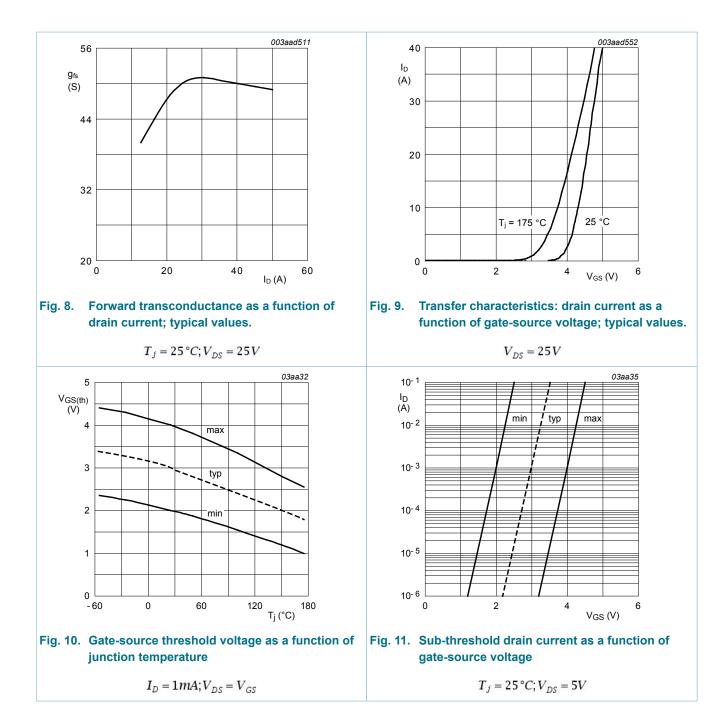


Fig. 7. Drain-source on-state resistance as a function of drain current; typical values.

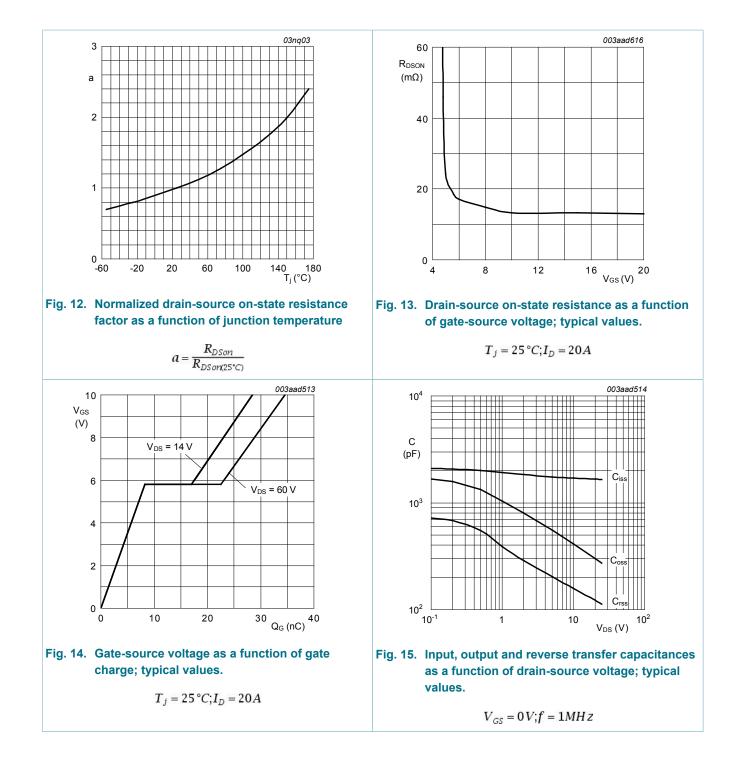
 $T_j = 25 \,^{\circ}C$

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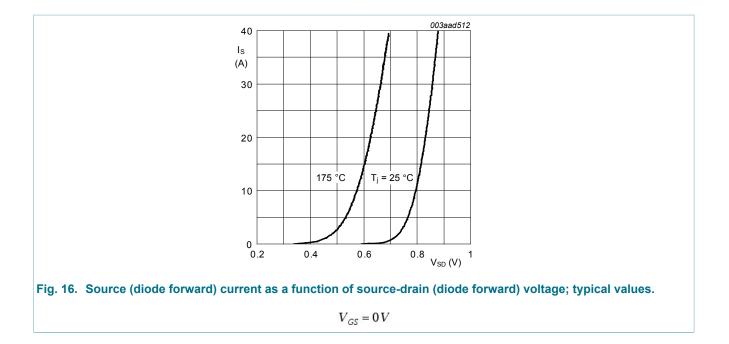
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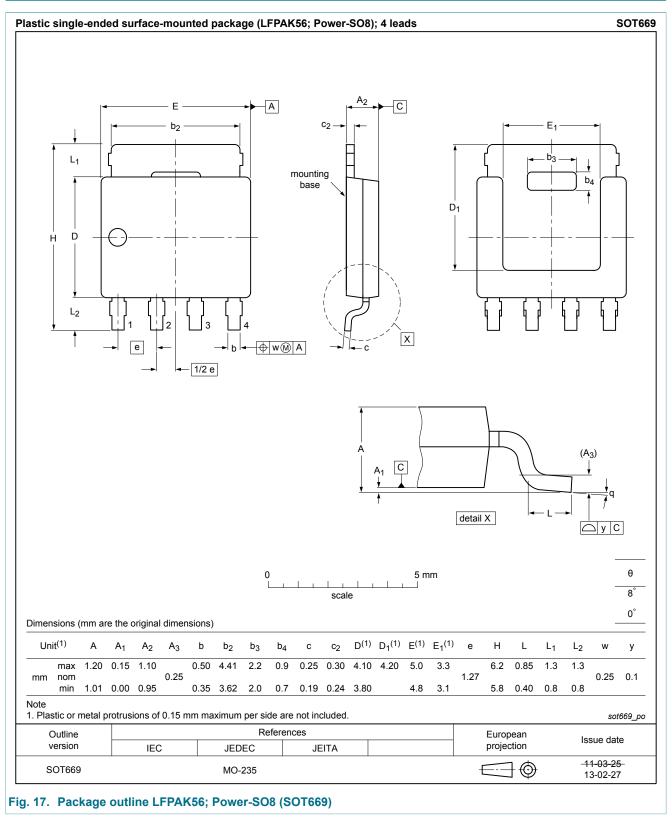
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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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